

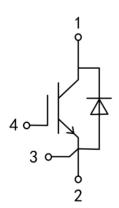
IGBT with Trench and Field-Stop technology, and SiC Schottky Barrier Diode (SBD)

WGH75R65FFC4

Features

- Vces=650V
- I_C=75A@ T_C=100°C
- Very low V_{CEsat}
- High speed switching
- Lower recovery losses SiC SBD
- High ruggedness
- RoHS compliant
- Halogen free





Applications

- Inverter
- Power factor correction(PFC)







Package pin definition	1	2	3	4	
	Collector	Emitter	Kelvin emitter	Gate	

Part	Package	Marking	Packing method	MPQ
WGH75R65FFC4	TO-247-4L	75R65FFC4	Tube	30/Tube





1 Maximum Ratings

Table 1 Maximum rated Values(T_c=25℃ unless otherwise specified)

Parameter	Symbol	Condition	Values	Unit
Collector to Emitter Voltage	V _{CES}		650	V
Gate to Emitter Voltage	V _{GES}		±20	V
Continuous Collector Current ¹			120	А
Continuous Collector Current	Ic	T _C =100°C	75	А
Pulsed Collector Current ²	I _{CM}		300	A
Diode Continuous Forward Current ¹	IF		70	А
Diode Continuous Forward Current		T _C =100°C	40	А
Diode Maximum Forward Current ²	I _{FM}		160	А
Maximum Dowar Dissination	P _{tot}		375	W
Maximum Power Dissipation		T _C =100 ℃	188	W
Operating Junction Temperature Range	TJ		-55~+175	℃
Storage Temperature Range	T _{STG}		-55~+150	℃
Thermal Resistance, Junction to case for IGBT	R _{th(J-C)}		0.40	K/W
Thermal Resistance, Junction to case for Diode	R _{th(J-C)}		0.95	K/W

Notes:

- 1. Calculated continuous current limited by package.
- 2. Pulse width limited by maximum junction temperature.





2 Electrical Characteristics, IGBT

Table 2 Characteristics Values(T_{C} =25 $^{\circ}$ C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Collector to Emitter Breakdown Voltage	BVces	I _C =250μΑ, V _{GE} =0V	650	-	-	V
0 1 5 0 1 1 1	VCE(sat)	I _C =75A, V _{GE} =15V	-	1.7	2.2	V
Collector to Emitter Saturation Voltage		I _C =75A, V _{GE} =15V, T _J =150℃	-	2.1	-	V
Gate Threshold Voltage	V _{GE(th)}	I _C =1mA, V _{GE} = V _{CE}	4.0	4.8	5.6	V
Zero Gate Voltage Collector current	I _{CES}	V _{CE} =650V, V _{GE} =0V	-	-	12	μA
Gate to Emitter Leakage Current	I _{GES}	V _{GE} =±20V, V _{CE} =0V	-	-	±250	nA
Interal Gate Resistor	RGint	f=1MHz, V _{AC} =25mV	-	0.7	-	Ω
Input Capacitance	Cies		-	3769	-	pF
Output Capacitance	Coes	f=1MHz, V _{CE} =30V, V _{GE} =0V	-	157	-	pF
Reverse Transfer Capacitance	Cres		-	46	-	pF
Total Gate charge	Q _G		-	128	-	nc
Gate to Emiter charge	Q _{GE}	V _{CC} =520V, I _C =75A, V _{GE} =15V	-	47	-	nc
Gate to Collector charge	Q _{GC}		-	65	-	nc
Turn-on Delay Time	t _{d(on)}		-	40	-	ns
Rising Time	t _r		-	44	-	ns
Turn-off Delay Time	t _{d(off)}	V _{CC} =400V, I _C =75A, V _{GE} =0/15V,	-	90	-	ns
Falling Time	t _f	R _G =10Ω, T _J =25℃ Inductive load	-	82	-	ns
Turn-on Switching Loss	Eon		-	1.0	-	mJ
Turn-off Switching Loss	E _{off}		-	1.2	-	mJ
Turn-on Delay Time	t _{d(on)}		-	38	-	ns
Rising Time	tr		-	48	-	ns
Turn-off Delay Time	t _{d(off)}	V _{CC} =400V, I _C =75A, V _{GE} =0/15V,	-	98	-	ns
Falling Time	t _f	R _G =10Ω, T _J =150°C Inductive load	-	94	-	ns
Turn-on Switching Loss	Eon		-	1.3	-	mJ
Turn-off Switching Loss	E _{off}		_	1.5	-	mJ





3 Electrical Characteristics, Diode

Table 3 Characteristics Values(T_c=25℃ unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
	.,	I _F =40A, T _J =25℃	-	1.4	1.9	V
Diode Forward Voltage	V _F	I _F =40A, T _J =150℃	-	1.7	-	V
Diode Peak Reverse Recovery Current	I _{rr}		-	12	-	А
Diode Reverse Recovery Time	t _{rr}	l _F =40A di/dt=-1300A/μs	_	20	-	ns
Diode Reverse Recovery Charge	Qrr	V _{CC} =400V T _J =25℃	-	134	-	nC
Reverse Recovery Energy	Erec		-	25	-	μJ
Diode Peak Reverse Recovery Current	Irr		-	12	-	А
Diode Reverse Recovery Time	t _{rr}	I _F =40A di/dt=-1300A/μs V _{CC} =400V T _J =150℃	-	20	-	ns
Diode Reverse Recovery Charge	Qrr		-	135	_	nC
Reverse Recovery Energy	Erec		-	24	-	μJ





4 Typical Characteristics diagrams

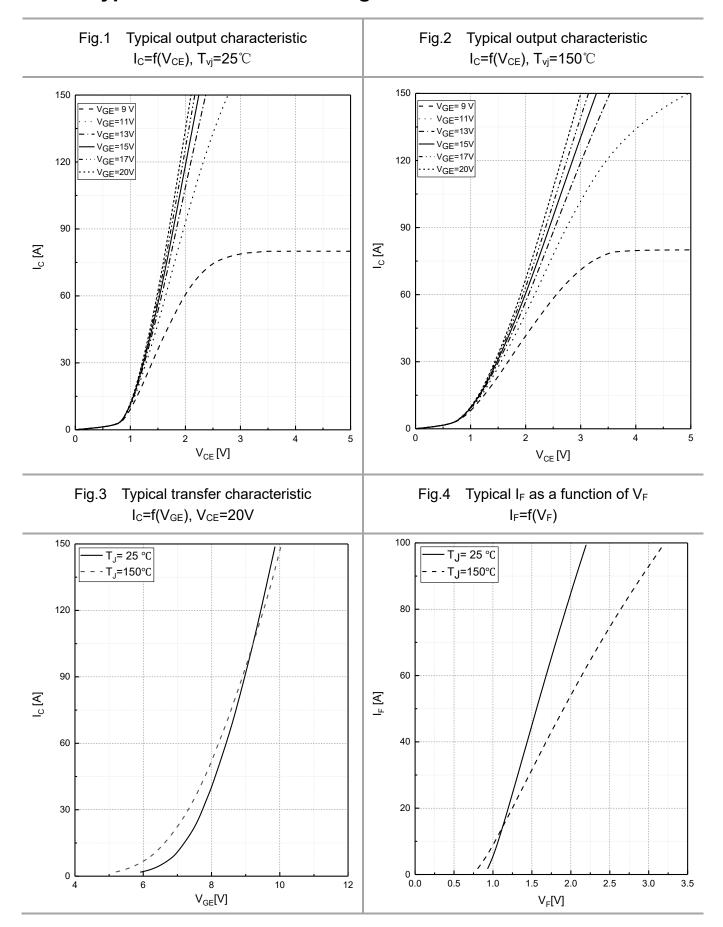
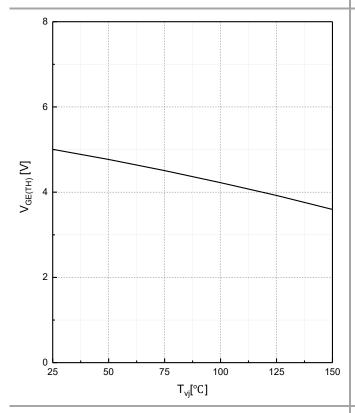




Fig.5 Typical $V_{GE(th)}$ as a function of T_{vj} V_{GEth} =f(T_{vj}), I_C =1mA

Fig.6 Typical V_{CEsat} as a function of T_{vj} V_{CEsat} =f(T_{vj}), V_{GE} =15V



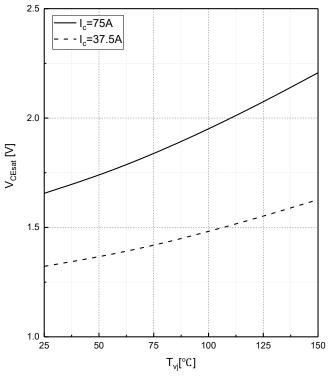
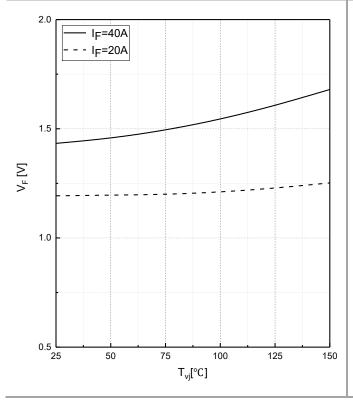


Fig.7 Typical V_F as a function of T_{vj} V_F =f(T_{vj})

Fig.8 Typical Gate charge V_{GE} =f(Q_G), I_C=75A



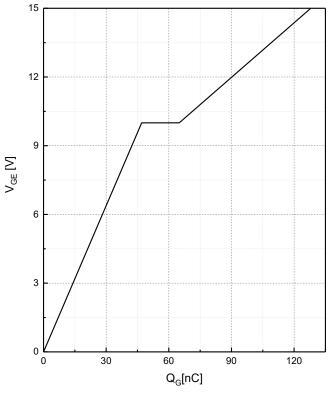




Fig.9 Typical switching energy losses as a function of R_{G}

E=f(R_G), V_{CC} =400V, I_{C} =75A, V_{GE} =0/15V, T_{J} =150°C

Fig.10 Typical switching energy losses as a function of I_C

E=f(I_C), V_{CC} =400V, R_{G} =10Ω, V_{GE} =0/15V, T_{J} =150°C

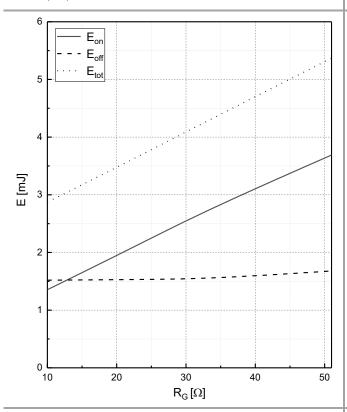
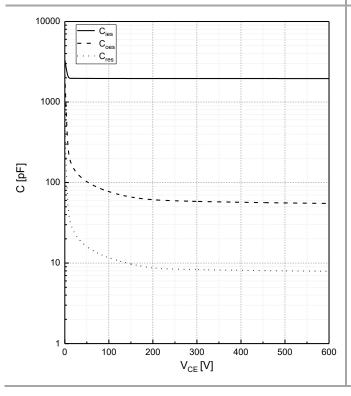


Fig.11 Typical capacitance as a function of V_{CE} $C=f(V_{CE})$, f=1MHz, $V_{GE}=0V$

Fig.12 Power dissipation as a function of T_C $P_{tot} = f(T_C), \ T_{vj} \le 175 \ ^{\circ}C$



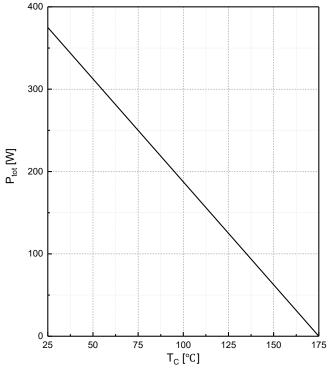
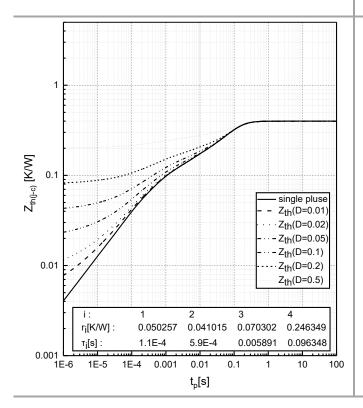
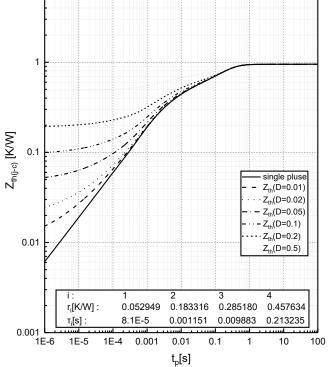




Fig.13 Transient thermal impedance of IGBT $Z_{th(j-c)}=f(t_p)$, $D=t_p/T$

Fig.14 Transient thermal impedance of Diode $Z_{th(j\text{-}c)}\text{=}f(t_p),\ D\text{=}t_p/T$

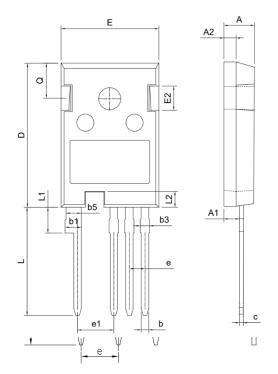


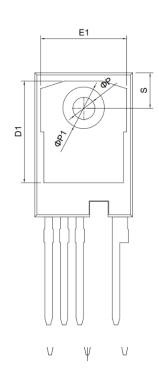






5 Package Outlines





CVMDOL	mm					
SYMBOL	MIN	NOM	MAX			
Α	4.80	5.00	5.21			
A1	2.21	2.41	2.61			
A2	1.80	2.00	2.20			
b	1.06	1.21	1.36			
b1	2.33	2.63	2.93			
b3	1.07	1.30	1.60			
b5	2.30	2.53	2.72			
С	0.51	0.61	0.75			
D	23.30	23.45	23.60			
D1	16.25	16.55	17.65			
Е	15.74	15.94	16.14			
E1	13.72	14.02	14.32			
E2	3.68	5.00	5.20			
e		2.54BSC				
e1		5.44BSC				
L	17.27	17.57	17.87			
L1	3.97	4.19	4.39			
L2	2.35	2.50	2.60			
ΦР	3.40	3.60	3.80			
ФР1	7.19REF					
Q	5.49	5.79	6.09			
S	6.00	6.17	6.40			

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1. The product specification aims to provide users with a reference regarding various product parameters, performance, and usage. It presents certain aspects of the product's performance in graphical form and is intended solely for users to select product and make product comparisons, enabling users to better understand and evaluate the characteristics and advantages of the product. It does not constitute any commitment, warranty, or guarantee.

2.The product parameters described in the product specification are numerical values, characteristics, and functions obtained through actual testing or theoretical calculations of the product in an independent or ideal state. Due to the complexity of product applications and variations in test conditions and equipment, there may be slight fluctuations in parameter test values. WAYON shall not guarantee that the actual performance of the product when installed in the customer's system or equipment will be entirely consistent with the product specification, especially concerning dynamic parameters. It is recommended that users consult with professionals for product selection and system design. Users should also thoroughly validate and assess whether the actual parameters and performance when installed in their respective systems or equipment meet their requirements or expectations. Additionally, users should exercise caution in verifying product compatibility issues, and WAYON assumes no responsibility for the application of the product.

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